

COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

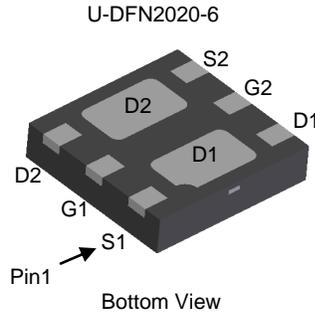
Device	V _{(BR)DSS}	R _{DS(ON)} max	I _D MAX T _A = +25°C
Q1 N-Channel	12V	29mΩ @ V _{GS} = 4.5V	5.6A
		34mΩ @ V _{GS} = 2.5V	5.1A
		44mΩ @ V _{GS} = 1.8V	4.5A
		65mΩ @ V _{GS} = 1.5V	3.7A
Q2 P-Channel	-12V	61mΩ @ V _{GS} = -4.5V	-3.8A
		81mΩ @ V _{GS} = -2.5V	-3.3A
		115mΩ @ V _{GS} = -1.8V	-2.8A
		210mΩ @ V _{GS} = -1.5V	-2.3A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

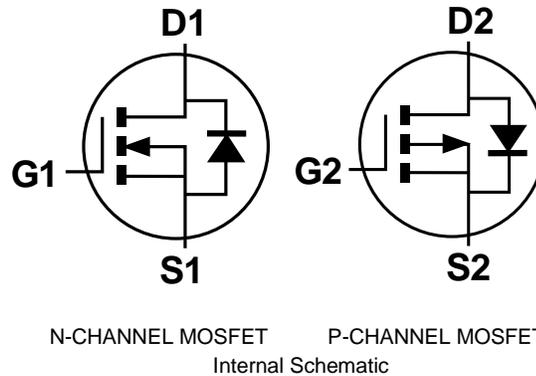


Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

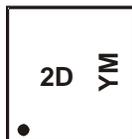


Ordering Information (Note 4)

Part Number	Case	Packaging
DMC1029UFDB -7	U-DFN2020-6	3000/Tape & Reel
DMC1029UFDB -13	U-DFN2020-6	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



2D = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: B = 2014)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020					
Code	B	C	D	E	F	G	H					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1 N-CHANNEL	Q2 P-CHANNEL	Units
Drain-Source Voltage			V _{DSS}	12	-12	V
Gate-Source Voltage			V _{GSS}	±8	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.6 4.4	-3.8 -3.0	A
	t < 5s	T _A = +25°C T _A = +70°C	I _D	7.2 5.8	-5.0 -4.0	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	1	-1	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	20	-15	A
Avalanche Current (L = 0.1mH)			I _{AS}	15	-12	A
Avalanche Energy (L = 0.1mH)			E _{AS}	12	8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P _D	1.4	W
	t < 5s		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	91	°C/W
	t < 5s		55	
Thermal Resistance, Junction to Case		R _{θJC}	20	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Note: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Electrical Characteristics Q1 N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	12	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.4	—	1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	17	29	mΩ	V _{GS} = 4.5V, I _D = 5A
		—	20	34		V _{GS} = 2.5V, I _D = 4.6A
		—	24	44		V _{GS} = 1.8V, I _D = 4.1A
		—	30	65		V _{GS} = 1.5V, I _D = 2A
Diode Forward Voltage	V _{SD}	—	0.6	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	914	—	pF	V _{DS} = 6V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	132	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	119	—	pF	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Gate Resistance	R _g	—	1.26	—	Ω	
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	10.5	—	nC	V _{DS} = 6V, I _D = 6.5A
Total Gate Charge (V _{GS} = 8V)		—	19.6	—	nC	
Gate-Source Charge	Q _{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.0	—	ns	
Turn-On Rise Time	t _r	—	10.5	—	ns	V _{DD} = 6V, V _{GS} = 4.5V, R _L = 1.2Ω, R _G = 1Ω
Turn-Off Delay Time	t _{D(OFF)}	—	16.6	—	ns	
Turn-Off Fall Time	t _f	—	4.1	—	ns	

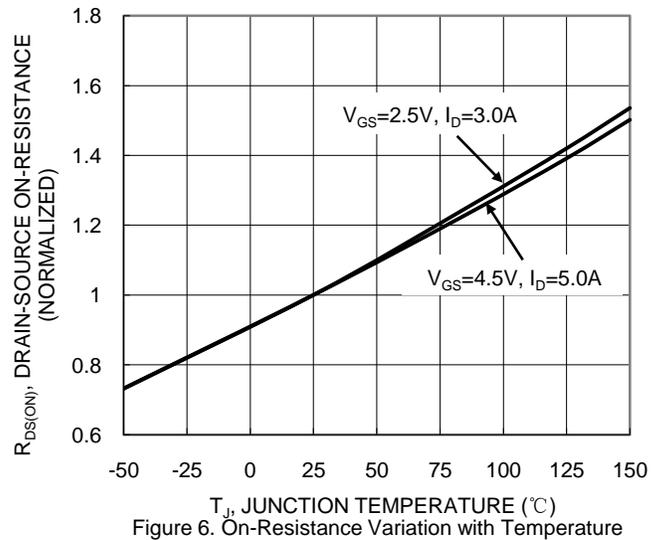
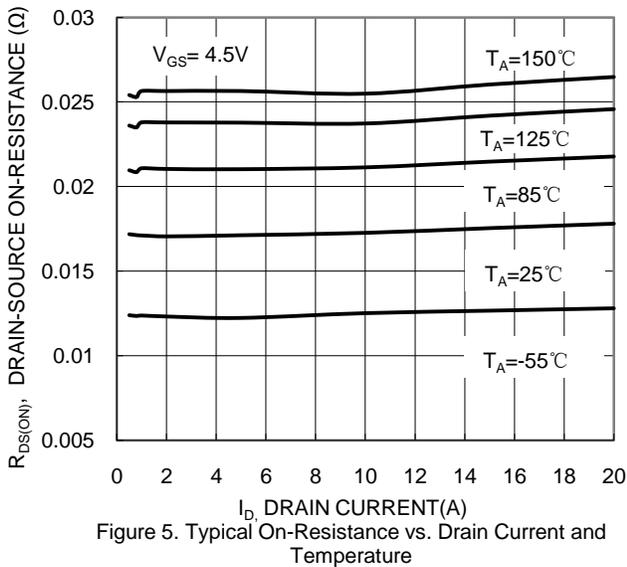
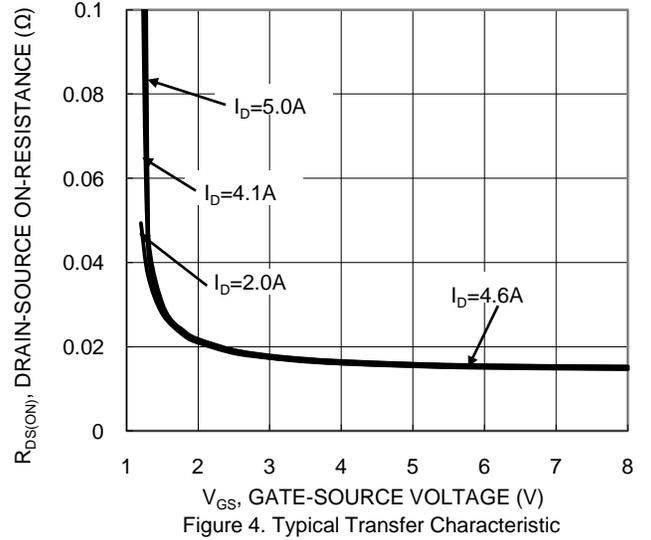
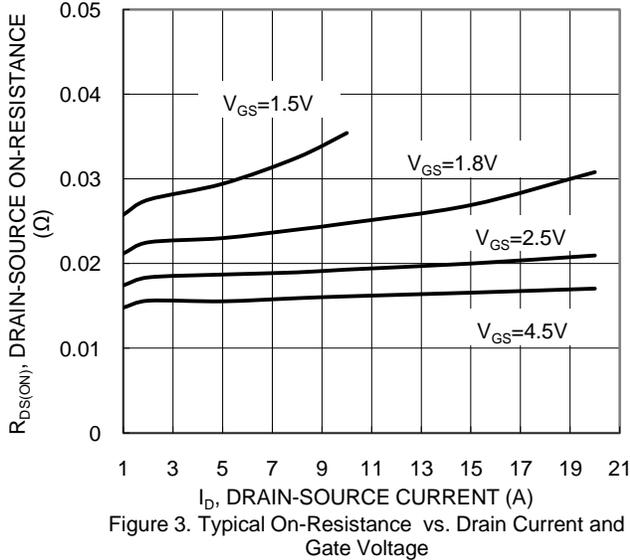
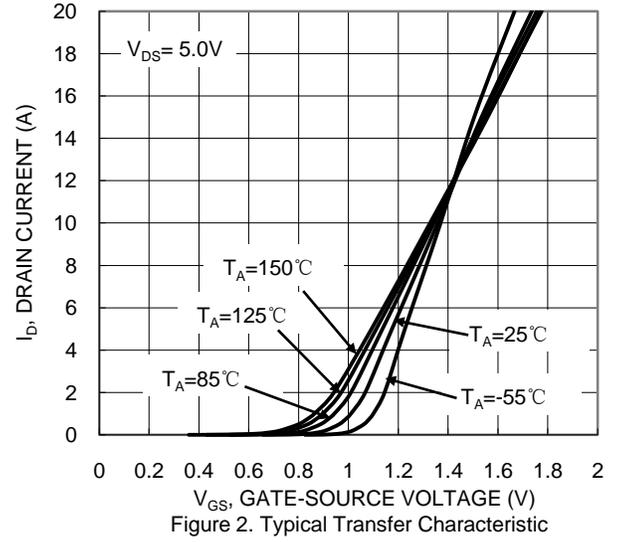
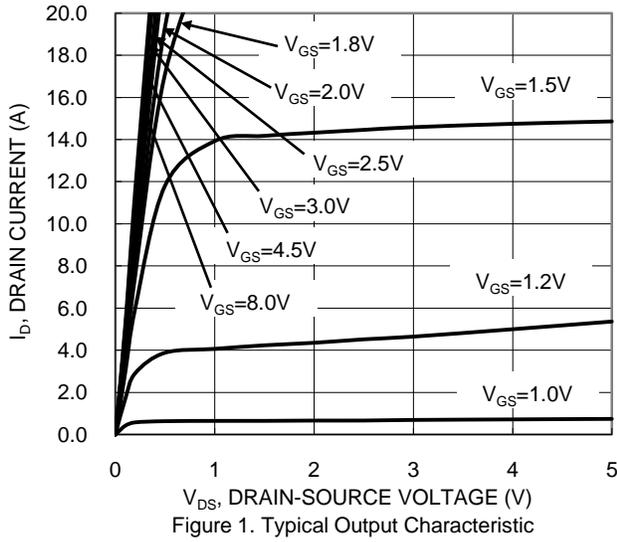
Electrical Characteristics Q2 P-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	37	61	mΩ	V _{GS} = -4.5V, I _D = -3.6A
		—	47	81		V _{GS} = -2.5V, I _D = -3.2A
		—	63	115		V _{GS} = -1.8V, I _D = -1A
		—	90	210		V _{GS} = -1.5V, I _D = -1A
Diode Forward Voltage	V _{SD}	—	-0.65	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	915	—	pF	V _{DS} = -6V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	225	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	183	—	pF	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Gate Resistance	R _g	—	56.9	—	Ω	
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	10.7	—	nC	V _{DS} = -6V, I _D = -4.3A
Total Gate Charge (V _{GS} = -8V)		—	17.9	—	nC	
Gate-Source Charge	Q _{gs}	—	1.7	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.0	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.7	—	ns	
Turn-On Rise Time	t _r	—	11.5	—	ns	V _{DD} = -6V, V _{GS} = -4.5V, R _L = 1.6Ω, R _G = 1Ω
Turn-Off Delay Time	t _{D(OFF)}	—	27.8	—	ns	
Turn-Off Fall Time	t _f	—	26.4	—	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

Typical Characteristics - N-CHANNEL

NEW PRODUCT



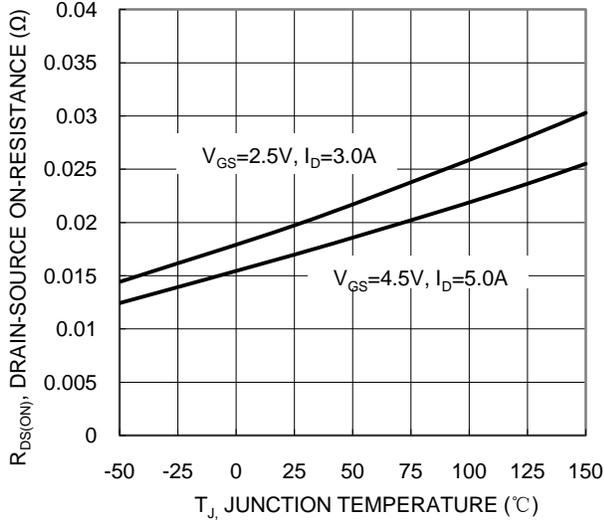


Figure 7. On-Resistance Variation with Temperature

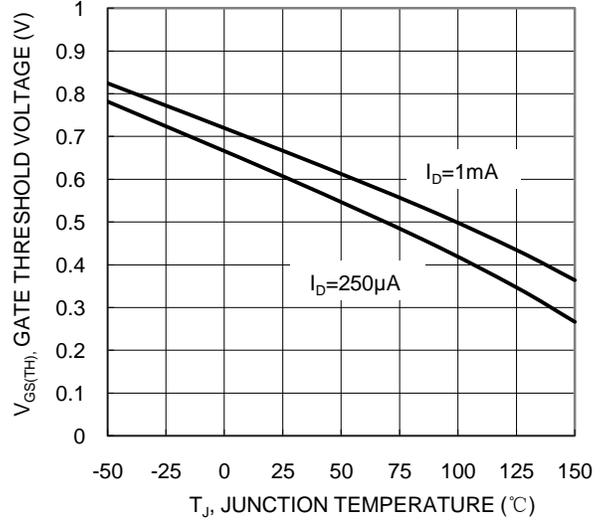


Figure 8. Gate Threshold Variation vs. Junction Temperature

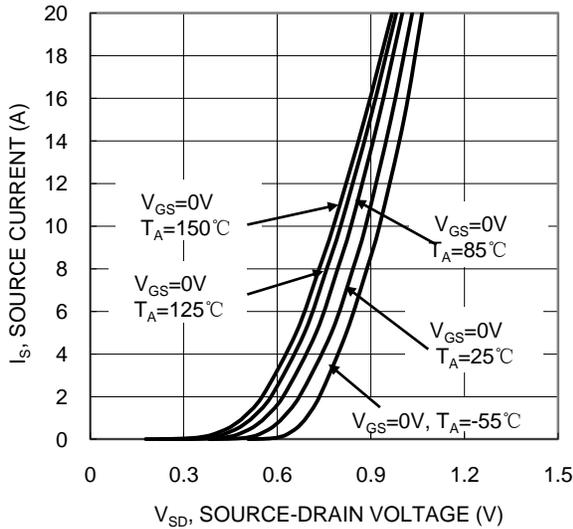


Figure 9. Diode Forward Voltage vs. Current

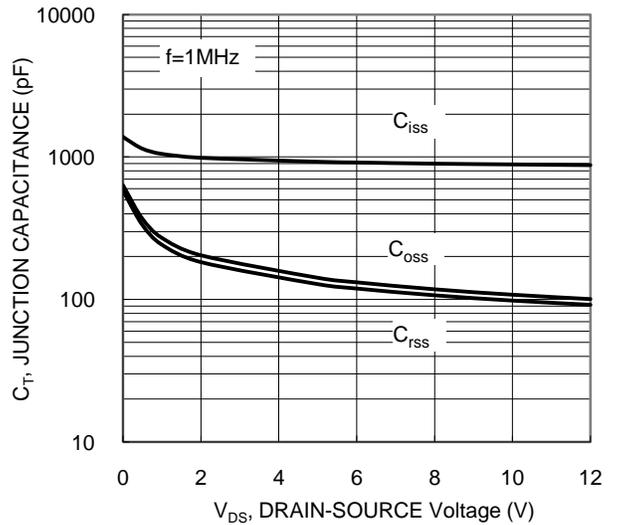


Figure 10. Typical Junction Capacitance

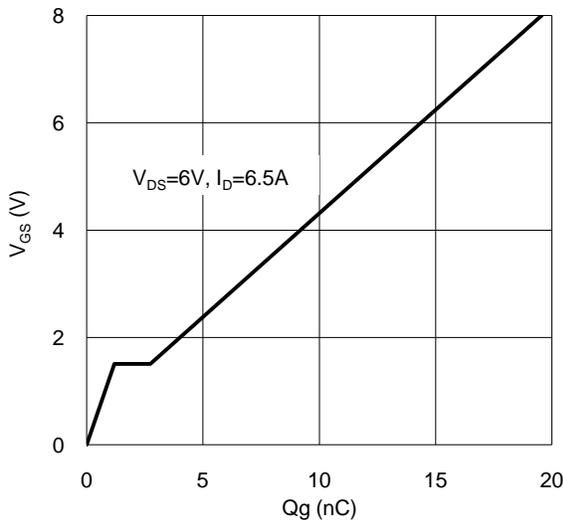


Figure 11. Gate Charge

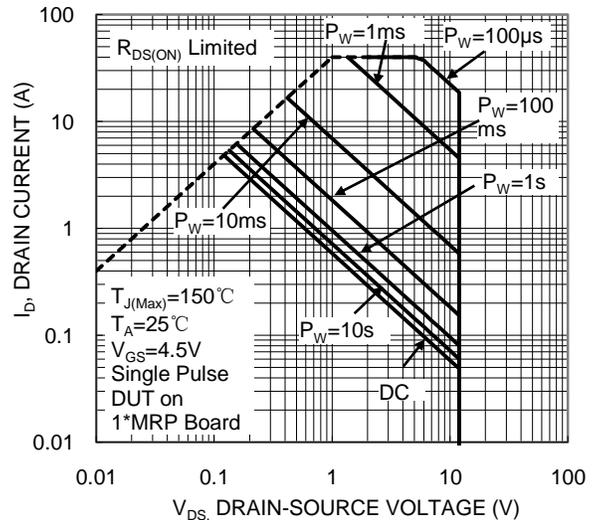


Figure 12. SOA, Safe Operation Area

Typical Characteristics - P-CHANNEL

NEW PRODUCT

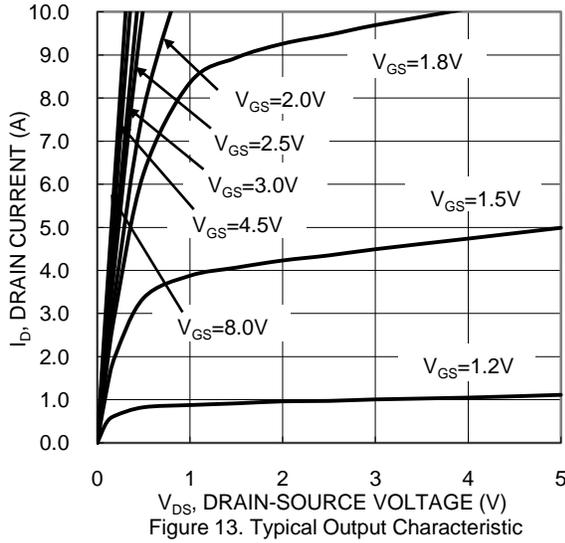


Figure 13. Typical Output Characteristic

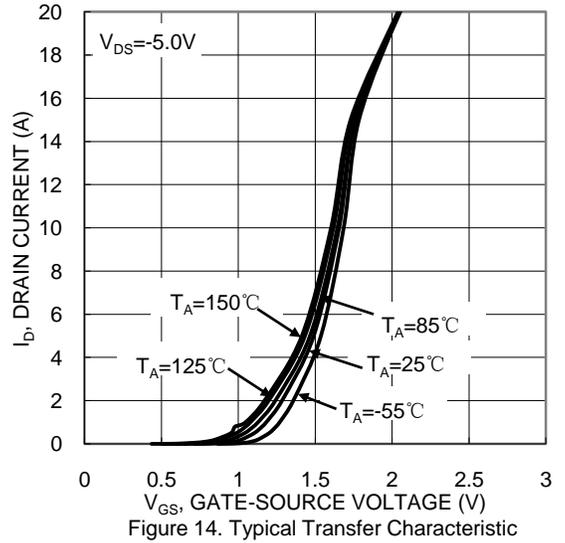


Figure 14. Typical Transfer Characteristic

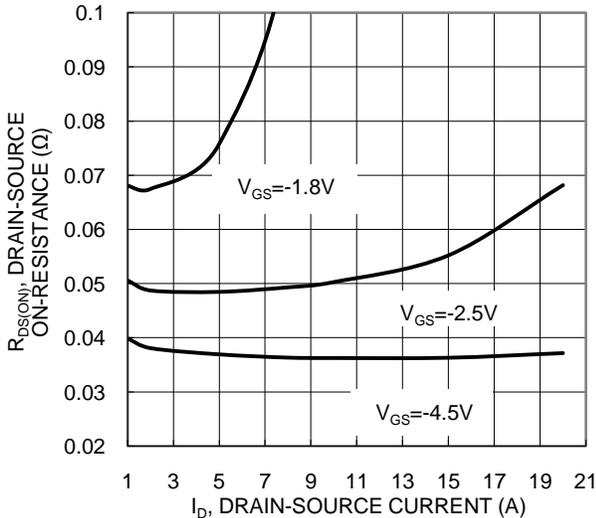


Figure 15. Typical On-Resistance vs Drain Current and Gate Voltage

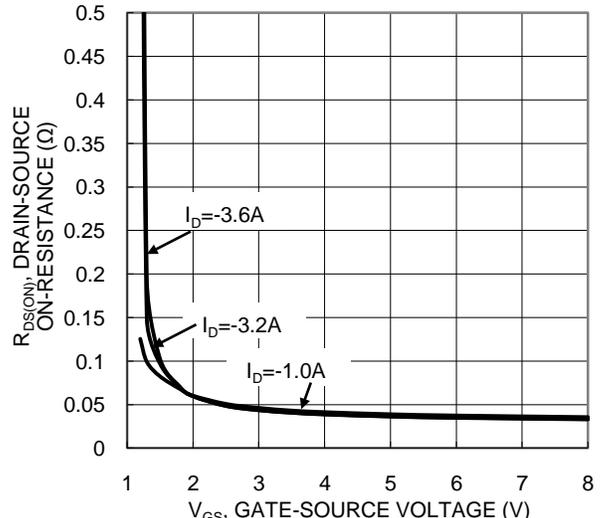


Figure 16. Typical Transfer Characteristic

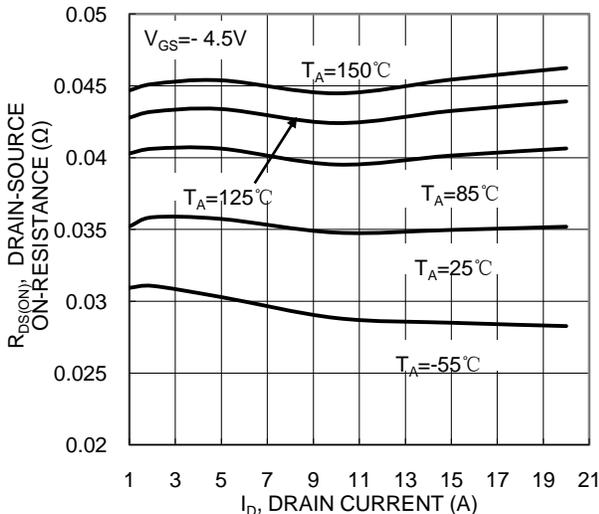


Figure 17. Typical On-Resistance vs Drain Current and Temperature

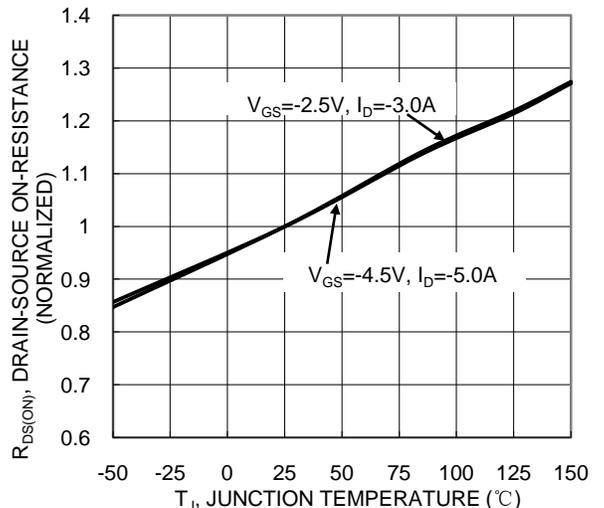


Figure 18. On-Resistance Variation with Temperature

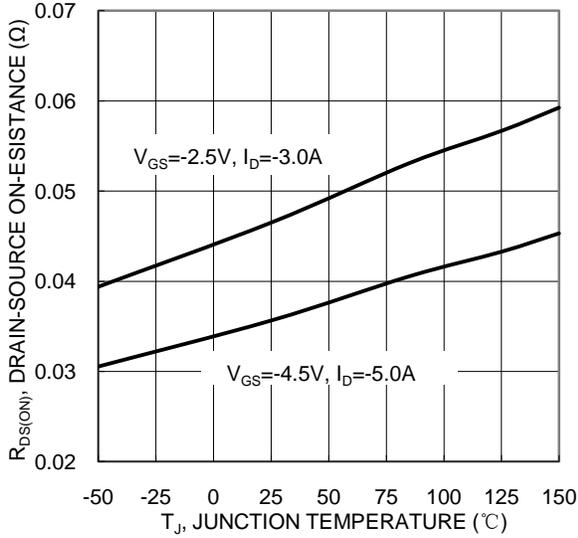


Figure 19. On-Resistance Variation with Temperature

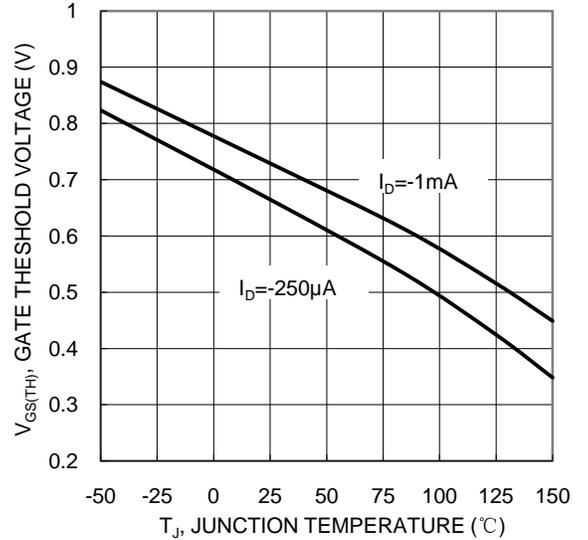


Figure 20. Gate Threshold Variation vs Junction Temperature

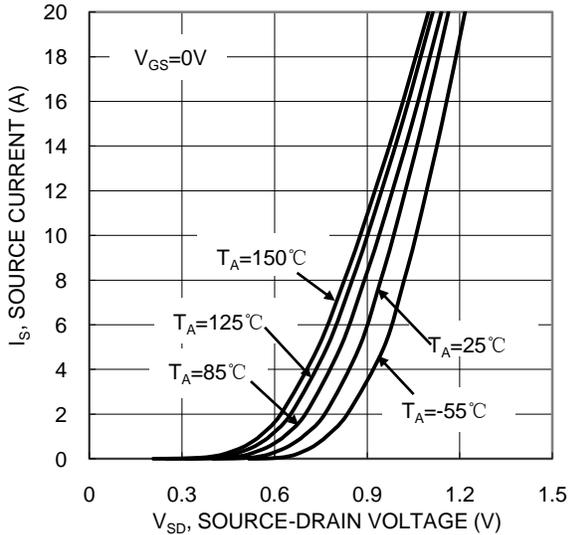


Figure 21. Diode Forward Voltage vs. Current

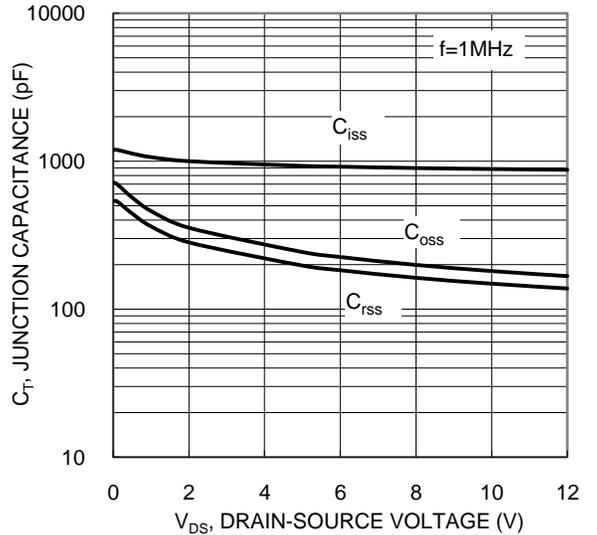


Figure 22. Typical Junction Capacitance

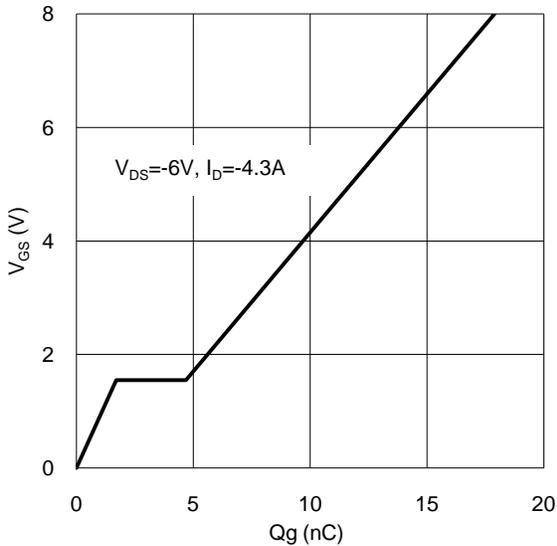


Figure 23. Gate Charge

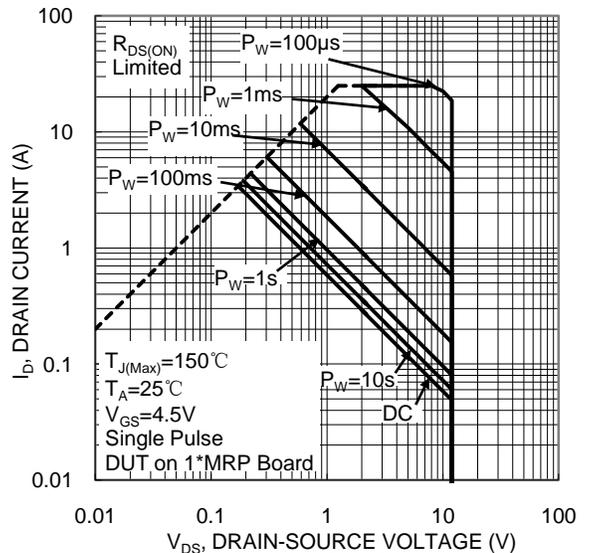


Figure 24. SOA, Safe Operation Area

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